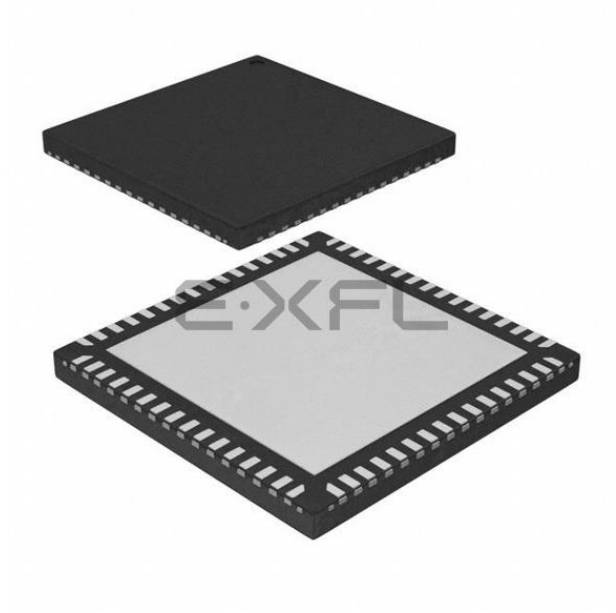

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	AVR
Core Size	8/16-Bit
Speed	32MHz
Connectivity	I²C, IrDA, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	50
Program Memory Size	64KB (32K x 16)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	64-QFN (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/atxmega64a3u-mnr

6. AVR CPU

6.1 Features

- 8/16-bit, high-performance Atmel AVR RISC CPU
  - 142 instructions
  - Hardware multiplier
- 32x8-bit registers directly connected to the ALU
- Stack in RAM
- Stack pointer accessible in I/O memory space
- Direct addressing of up to 16MB of program memory and 16MB of data memory
- True 16/24-bit access to 16/24-bit I/O registers
- Efficient support for 8-, 16-, and 32-bit arithmetic
- Configuration change protection of system-critical features

6.2 Overview

All Atmel AVR XMEGA devices use the 8/16-bit AVR CPU. The main function of the CPU is to execute the code and perform all calculations. The CPU is able to access memories, perform calculations, control peripherals, and execute the program in the flash memory. Interrupt handling is described in a separate section, refer to “Interrupts and Programmable Multilevel Interrupt Controller” on page 30.

6.3 Architectural Overview

In order to maximize performance and parallelism, the AVR CPU uses a Harvard architecture with separate memories and buses for program and data. Instructions in the program memory are executed with single-level pipelining. While one instruction is being executed, the next instruction is pre-fetched from the program memory. This enables instructions to be executed on every clock cycle. For details of all AVR instructions, refer to http://www.atmel.com/avr.

7.3.4 Production Signature Row

The production signature row is a separate memory section for factory programmed data. It contains calibration data for functions such as oscillators and analog modules. Some of the calibration values will be automatically loaded to the corresponding module or peripheral unit during reset. Other values must be loaded from the signature row and written to the corresponding peripheral registers from software. For details on calibration conditions, refer to “Electrical Characteristics” on page 73.

The production signature row also contains an ID that identifies each microcontroller device type and a serial number for each manufactured device. The serial number consists of the production lot number, wafer number, and wafer coordinates for the device. The device ID for the available devices is shown in Table 7-2.

The production signature row cannot be written or erased, but it can be read from application software and external programmers.

Table 7-2. Device ID bytes for Atmel AVR XMEGA A3U devices.

Device	Device ID bytes		
	Byte 2	**Byte 1**	**Byte 0**
ATxmega64A3U	42	96	1E
ATxmega128A3U	42	97	1E
ATxmega192A3U	44	97	1E
ATxmega256A3U	42	98	1E

7.3.5 User Signature Row

The user signature row is a separate memory section that is fully accessible (read and write) from application software and external programmers. It is one flash page in size, and is meant for static user parameter storage, such as calibration data, custom serial number, identification numbers, random number seeds, etc. This section is not erased by chip erase commands that erase the flash, and requires a dedicated erase command. This ensures parameter storage during multiple program/erase operations and on-chip debug sessions.

7.4 Fuses and Lock bits

The fuses are used to configure important system functions, and can only be written from an external programmer. The application software can read the fuses. The fuses are used to configure reset sources such as brownout detector and watchdog, startup configuration, JTAG enable, and JTAG user ID.

The lock bits are used to set protection levels for the different flash sections (that is, if read and/or write access should be blocked). Lock bits can be written by external programmers and application software, but only to stricter protection levels. Chip erase is the only way to erase the lock bits. To ensure that flash contents are protected even during chip erase, the lock bits are erased after the rest of the flash memory has been erased.

An unprogrammed fuse or lock bit will have the value one, while a programmed fuse or lock bit will have the value zero.

Both fuses and lock bits are reprogrammable like the flash program memory.

7.5 Data Memory

The data memory contains the I/O memory, internal SRAM, optionally memory mapped EEPROM, and external memory if available. The data memory is organized as one continuous memory section, see Table 7-3 on page 16. To simplify development, I/O Memory, EEPROM and SRAM will always have the same start addresses for all Atmel AVR XMEGA devices.

29. DAC – 12-bit Digital to Analog Converter

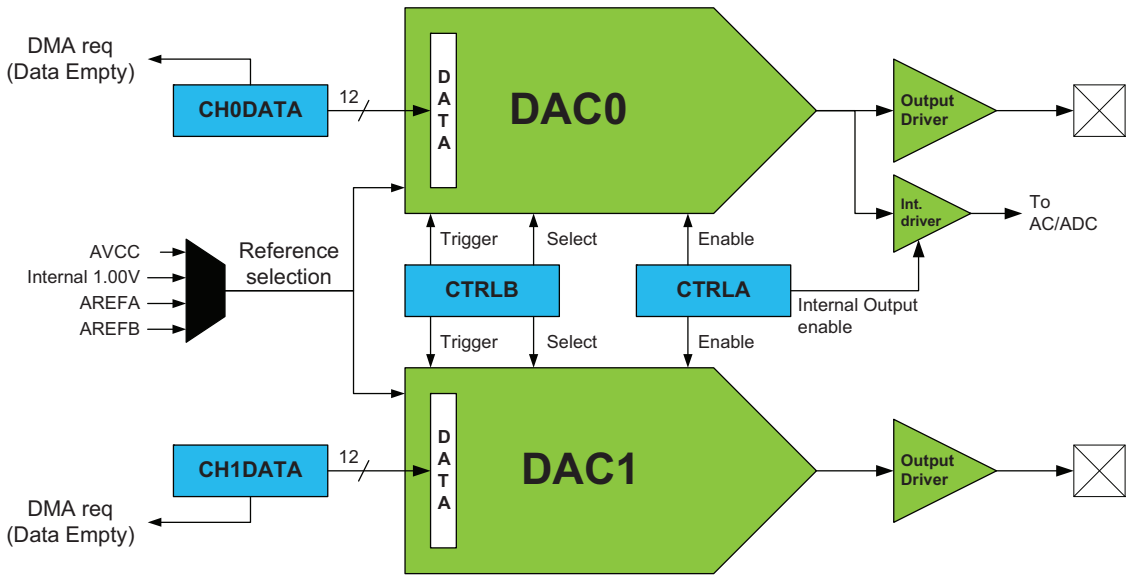
29.1 Features

- One Digital to Analog Converter (DAC)
- 12-bit resolution
- Two independent, continuous-drive output channels
- Up to one million samples per second conversion rate per DAC channel
- Built-in calibration that removes:
  - Offset error
  - Gain error
- Multiple conversion trigger sources
  - On new available data
  - Events from the event system
- High drive capabilities and support for
  - Resistive loads
  - Capacitive loads
  - Combined resistive and capacitive loads
- Internal and external reference options
- DAC output available as input to analog comparator and ADC
- Low-power mode, with reduced drive strength
- Optional DMA transfer of data

29.2 Overview

The digital-to-analog converter (DAC) converts digital values to voltages. The DAC has two channels, each with 12-bit resolution, and is capable of converting up to one million samples per second (msps) on each channel. The built-in calibration system can remove offset and gain error when loaded with calibration values from software.

Figure 29-1. DAC overview.



Mnemonics	Operands	Description	Operation	Flags	#Clocks
LDS	Rd, k	Load Direct from data space	Rd ← (k)	None	2 (1)(2)
LD	Rd, X	Load Indirect	Rd ← (X)	None	1 (1)(2)
LD	Rd, X+	Load Indirect and Post-Increment	Rd ← (X) X ← X + 1	None	1 (1)(2)
LD	Rd, -X	Load Indirect and Pre-Decrement	X ← X - 1, ← X - 1 Rd ← (X) ← (X)	None	2 (1)(2)
LD	Rd, Y	Load Indirect	Rd ← (Y) ← (Y)	None	1 (1)(2)
LD	Rd, Y+	Load Indirect and Post-Increment	Rd ← (Y) Y ← Y + 1	None	1 (1)(2)
LD	Rd, -Y	Load Indirect and Pre-Decrement	Y ← Y - 1 Rd ← (Y)	None	2 (1)(2)
LDD	Rd, Y+q	Load Indirect with Displacement	Rd ← (Y + q)	None	2 (1)(2)
LD	Rd, Z	Load Indirect	Rd ← (Z)	None	1 (1)(2)
LD	Rd, Z+	Load Indirect and Post-Increment	Rd ← (Z), Z ← Z+1	None	1 (1)(2)
LD	Rd, -Z	Load Indirect and Pre-Decrement	Z ← Z - 1, Rd ← (Z)	None	2 (1)(2)
LDD	Rd, Z+q	Load Indirect with Displacement	Rd ← (Z + q)	None	2 (1)(2)
STS	k, Rr	Store Direct to Data Space	(k) ← Rd	None	2 (1)
ST	X, Rr	Store Indirect	(X) ← Rr	None	1 (1)
ST	X+, Rr	Store Indirect and Post-Increment	(X) ← Rr, X ← X + 1	None	1 (1)
ST	-X, Rr	Store Indirect and Pre-Decrement	X ← X - 1, (X) ← Rr	None	2 (1)
ST	Y, Rr	Store Indirect	(Y) ← Rr	None	1 (1)
ST	Y+, Rr	Store Indirect and Post-Increment	(Y) ← Rr, Y ← Y + 1	None	1 (1)
ST	-Y, Rr	Store Indirect and Pre-Decrement	Y ← Y - 1, (Y) ← Rr	None	2 (1)
STD	Y+q, Rr	Store Indirect with Displacement	(Y + q) ← Rr	None	2 (1)
ST	Z, Rr	Store Indirect	(Z) ← Rr	None	1 (1)
ST	Z+, Rr	Store Indirect and Post-Increment	(Z) ← Rr Z ← Z + 1	None	1 (1)
ST	-Z, Rr	Store Indirect and Pre-Decrement	Z ← Z - 1	None	2 (1)
STD	Z+q,Rr	Store Indirect with Displacement	(Z + q) ← Rr	None	2 (1)
LPM		Load Program Memory	R0 ← (Z)	None	3
LPM	Rd, Z	Load Program Memory	Rd ← (Z)	None	3
LPM	Rd, Z+	Load Program Memory and Post-Increment	Rd ← (Z), Z ← Z + 1	None	3
ELPM		Extended Load Program Memory	R0 ← (RAMPZ:Z)	None	3
ELPM	Rd, Z	Extended Load Program Memory	Rd ← (RAMPZ:Z)	None	3
ELPM	Rd, Z+	Extended Load Program Memory and Post-Increment	Rd ← (RAMPZ:Z), Z ← Z + 1	None	3
SPM		Store Program Memory	(RAMPZ:Z) ← R1:R0	None	-
SPM	Z+	Store Program Memory and Post-Increment by 2	(RAMPZ:Z) ← R1:R0, Z ← Z + 2	None	-

Table 36-5. Current consumption for modules and peripherals.

Symbol	Parameter	Condition[1]		Min.	Typ.	Max.	Units
I_{CC}	ULP oscillator				1.0		µA
	32.768kHz int. oscillator				26		µA
	2MHz int. oscillator				85		µA
		DFLL enabled with 32.768kHz int. osc. as reference			115		
	32MHz int. oscillator				270		µA
		DFLL enabled with 32.768kHz int. osc. as reference			460		
	PLL	20x multiplication factor, 32MHz int. osc. DIV4 as reference			220		µA
	Watchdog Timer				1		µA
	BOD	Continuous mode			138		µA
		Sampled mode, includes ULP oscillator			1.2		
	Internal 1.0V reference				100		µA
	Temperature sensor				95		µA
	ADC	250ksps V_{REF} = Ext ref			3.0		mA
			CURRLIMIT = LOW		2.6		
			CURRLIMIT = MEDIUM		2.1		
			CURRLIMIT = HIGH		1.6		
	DAC	250ksps V_{REF} = Ext ref No load	Normal mode		1.9		mA
			Low Power mode		1.1		
	AC	High Speed Mode			330		µA
		Low Power Mode			130		
	DMA	615KBps between I/O registers and SRAM			115		µA
	Timer/Counter				16		µA
	USART	Rx and Tx enabled, 9600 BAUD			2.5		µA
	Flash memory and EEPROM programming				4		mA

Note: 1. All parameters measured as the difference in current consumption between module enabled and disabled. All data at V_{CC} = 3.0V, Clk_{SYS} = 1MHz external clock without prescaling, T = 25°C unless other conditions are given.

Table 36-28. External clock with prescaler [1] for system clock.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
$1/t_{CK}$	Clock Frequency [2]	V_{CC} = 1.6 - 1.8V	0		90	MHz
		V_{CC} = 2.7 - 3.6V	0		142	
t_{CK}	Clock Period	V_{CC} = 1.6 - 1.8V	11			ns
		V_{CC} = 2.7 - 3.6V	7			
t_{CH}	Clock High Time	V_{CC} = 1.6 - 1.8V	4.5			ns
		V_{CC} = 2.7 - 3.6V	2.4			
t_{CL}	Clock Low Time	V_{CC} = 1.6 - 1.8V	4.5			ns
		V_{CC} = 2.7 - 3.6V	2.4			
t_{CR}	Rise Time (for maximum frequency)	V_{CC} = 1.6 - 1.8V			1.5	ns
		V_{CC} = 2.7 - 3.6V			1.0	
t_{CF}	Fall Time (for maximum frequency)	V_{CC} = 1.6 - 1.8V			1.5	ns
		V_{CC} = 2.7 - 3.6V			1.0	
Δt_{CK}	Change in period from one clock cycle to the next				10	%

Notes:
1. System Clock Prescalers must be set so that maximum CPU clock frequency for device is not exceeded.
2. The maximum frequency vs. supply voltage is linear between 1.6V and 2.7V, and the same applies for all other parameters with supply voltage conditions.

36.1.14.7 External 16MHz crystal oscillator and XOSC characteristics

Table 36-29. External 16MHz crystal oscillator and XOSC characteristics.

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
	Cycle to cycle jitter	XOSCPWR=0	FRQRANGE=0		<10		ns
			FRQRANGE=1, 2, or 3		<1		
		XOSCPWR=1			<1		
	Long term jitter	XOSCPWR=0	FRQRANGE=0		<6		ns
			FRQRANGE=1, 2, or 3		<0.5		
		XOSCPWR=1			<0.5		
	Frequency error	XOSCPWR=0	FRQRANGE=0		<0.1		%
			FRQRANGE=1		<0.05		
			FRQRANGE=2 or 3		<0.005		
		XOSCPWR=1			<0.005		
	Duty cycle	XOSCPWR=0	FRQRANGE=0		40		%
			FRQRANGE=1		42		
			FRQRANGE=2 or 3		45		
		XOSCPWR=1			48		

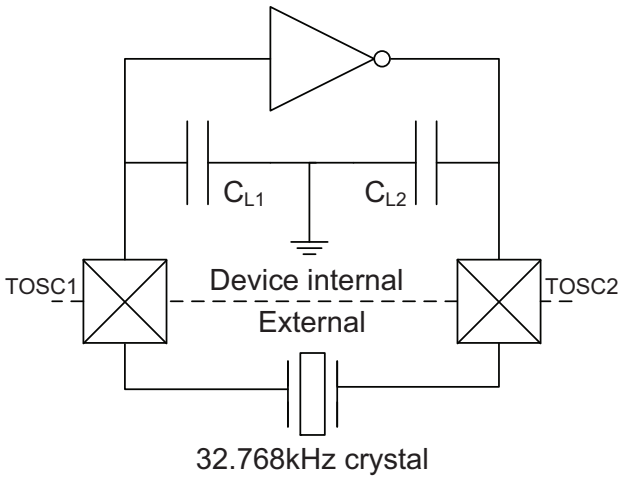
36.1.14.8 External 32.768kHz crystal oscillator and TOSC characteristics

Table 36-30. External 32.768kHz crystal oscillator and TOSC characteristics.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
ESR/R1	Recommended crystal equivalent series resistance (ESR)	Crystal load capacitance 6.5pF			60	kΩ
		Crystal load capacitance 9.0pF			35	
C_{TOSC1}	Parasitic capacitance TOSC1 pin			4.2		pF
C_{TOSC2}	Parasitic capacitance TOSC2 pin			4.3		pF
	Recommended safety factor	capacitance load matched to crystal specification	3			

Note: 1. See Figure 36-4 for definition.

Figure 36-4. TOSC input capacitance.



The parasitic capacitance between the TOSC pins is C_{L1} + C_{L2} in series as seen from the crystal when oscillating without external capacitors.

Table 36-60. External clock with prescaler [1] for system clock.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
$1/t_{CK}$	Clock Frequency [2]	V_{CC} = 1.6 - 1.8V	0		90	MHz
		V_{CC} = 2.7 - 3.6V	0		142	
t_{CK}	Clock Period	V_{CC} = 1.6 - 1.8V	11			ns
		V_{CC} = 2.7 - 3.6V	7			
t_{CH}	Clock High Time	V_{CC} = 1.6 - 1.8V	4.5			ns
		V_{CC} = 2.7 - 3.6V	2.4			
t_{CL}	Clock Low Time	V_{CC} = 1.6 - 1.8V	4.5			ns
		V_{CC} = 2.7 - 3.6V	2.4			
t_{CR}	Rise Time (for maximum frequency)	V_{CC} = 1.6 - 1.8V			1.5	ns
		V_{CC} = 2.7 - 3.6V			1.0	
t_{CF}	Fall Time (for maximum frequency)	V_{CC} = 1.6 - 1.8V			1.5	ns
		V_{CC} = 2.7 - 3.6V			1.0	
Δt_{CK}	Change in period from one clock cycle to the next				10	%

Notes:
1. System Clock Prescalers must be set so that maximum CPU clock frequency for device is not exceeded.
2. The maximum frequency vs. supply voltage is linear between 1.6V and 2.7V, and the same applies for all other parameters with supply voltage conditions.

36.2.14.7 External 16MHz crystal oscillator and XOSC characteristics

Table 36-61. External 16MHz crystal oscillator and XOSC characteristics.

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
	Cycle to cycle jitter	XOSCPWR=0	FRQRANGE=0		<10		ns
			FRQRANGE=1, 2, or 3		<1		
		XOSCPWR=1			<1		
	Long term jitter	XOSCPWR=0	FRQRANGE=0		<6		ns
			FRQRANGE=1, 2, or 3		<0.5		
		XOSCPWR=1			<0.5		
	Frequency error	XOSCPWR=0	FRQRANGE=0		<0.1		%
			FRQRANGE=1		<0.05		
			FRQRANGE=2 or 3		<0.005		
		XOSCPWR=1			<0.005		
	Duty cycle	XOSCPWR=0	FRQRANGE=0		40		%
			FRQRANGE=1		42		
			FRQRANGE=2 or 3		45		
		XOSCPWR=1			48		

36.3.11 External Reset Characteristics

Table 36-82. External reset characteristics.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
t_{EXT}	Minimum reset pulse width			95	1000	ns
V_{RST}	Reset threshold voltage (V_{IH})	V_{CC} = 2.7 - 3.6V		0.60*V_{CC}		V
		V_{CC} = 1.6 - 2.7V		0.70*V_{CC}		
	Reset threshold voltage (V_{IL})	V_{CC} = 2.7 - 3.6V		0.40*V_{CC}		
		V_{CC} = 1.6 - 2.7V		0.30*V_{CC}		
R_{RST}	Reset pin Pull-up Resistor			25		kΩ

36.3.12 Power-on Reset Characteristics

Table 36-83. Power-on reset characteristics.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
V_{POT-} [1]	POR threshold voltage falling V_{CC}	V_{CC} falls faster than 1V/ms	0.4	1.0		V
		V_{CC} falls at 1V/ms or slower	0.8	1.0		
V_{POT+}	POR threshold voltage rising V_{CC}			1.3	1.59	V

Note: 1. V_{POT-} values are only valid when BOD is disabled. When BOD is enabled V_{POT-} = V_{POT+}.

36.3.13 Flash and EEPROM Memory Characteristics

Table 36-84. Endurance and data retention.

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
	Flash	Write/Erase cycles	25°C	10K			Cycle
			85°C	10K			
			105°C	2K			
		Data retention	25°C	100			Year
			85°C	25			
			105°C	10			
	EEPROM	Write/Erase cycles	25°C	100K			Cycle
			85°C	100K			
			105°C	30K			
		Data retention	25°C	100			Year
			85°C	25			
			105°C	10			

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
	Offset Error, input referred	1x gain, normal mode			-2		mV
		8x gain, normal mode			-5		
		64x gain, normal mode			-4		
	Noise	1x gain, normal mode	V_{CC} = 3.6V Ext. V_{REF}		0.5		mV rms
		8x gain, normal mode			1.5		
		64x gain, normal mode			11		

Note: 1. Maximum numbers are based on characterisation and not tested in production, and valid for 5% to 95% input voltage range.

36.4.7 DAC Characteristics

Table 36-108. Power supply, reference and output range.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
AV_{CC}	Analog supply voltage		V_{CC}- 0.3		V_{CC}+ 0.3	
AV_{REF}	External reference voltage		1.0		V_{CC}- 0.6	V
$R_{channel}$	DC output impedance				50	Ω
	Linear output voltage range		0.15		AV_{CC}-0.15	V
R_{AREF}	Reference input resistance			>10		MΩ
CAREF	Reference input capacitance	Static load		7		pF
	Minimum Resistance load		1			kΩ
	Maximum capacitance load				100	pF
		1000Ω serial resistance			1	nF
	Output sink/source	Operating within accuracy specification			AV_{CC}/1000	mA
		Safe operation			10	

Table 36-109. Clock and timing.

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
f_{DAC}	Conversion rate	C_{load}=100pF, maximum step size	Normal mode	0		1000	ksps
			Low power mode	0		500	

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
t_{delay}	Propagation delay	V_{CC} = 3.0V, T= 85°C	mode = HS		30	90	ns
		mode = HS			30		
		V_{CC} = 3.0V, T= 85°C	mode = LP		130	500	
		mode = LP			130		
	64-Level Voltage Scaler	Integral non-linearity (INL)			0.3	0.5	lsb

36.4.9 Bandgap and Internal 1.0V Reference Characteristics

Table 36-112. Bandgap and Internal 1.0V reference characteristics.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
	Startup time	As reference for ADC or DAC	1 Clk_{PER} + 2.5µs			µs
		As input voltage to ADC and AC		1.5		
	Bandgap voltage			1.1		V
INT1V	Internal 1.00V reference	T= 85°C, after calibration	0.99	1	1.01	V
	Variation over voltage and temperature	Relative to T= 85°C, V_{CC} = 3.0V		±1.0		%

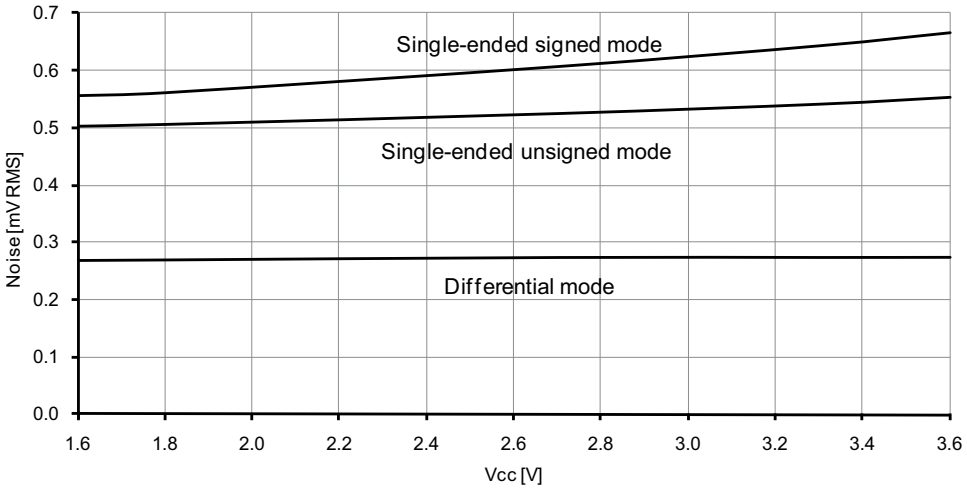
36.4.10 Brownout Detection Characteristics

Table 36-113. Brownout detection characteristics.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
V_{BOT}	BOD level 0 falling V_{CC}		1.60	1.62	1.72	V
	BOD level 1 falling V_{CC}			1.8		
	BOD level 2 falling V_{CC}			2.0		
	BOD level 3 falling V_{CC}			2.2		
	BOD level 4 falling V_{CC}			2.4		
	BOD level 5 falling V_{CC}			2.6		
	BOD level 6 falling V_{CC}			2.8		
	BOD level 7 falling V_{CC}			3.0		
t_{BOD}	Detection time	Continuous mode		0.4		µs
		Sampled mode		1000		
V_{HYST}	Hysteresis			1.6		%

Figure 37-47. Noise vs. V_{CC}.

T = 25°C, V_{REF} = external 1.0V, ADC sampling speed = 500ksps.



37.1.4 DAC Characteristics

Figure 37-48. DAC INL error vs. V_{REF}.

V_{CC} = 3.6V.

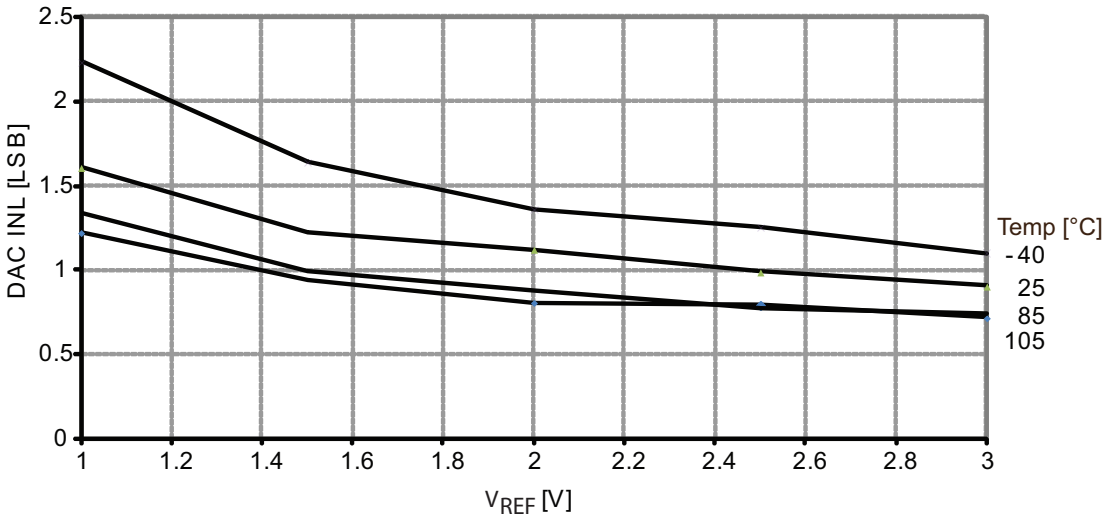


Figure 37-63. Reset pin pull-up resistor current vs. reset pin voltage.

V_{CC} = 3.0V.

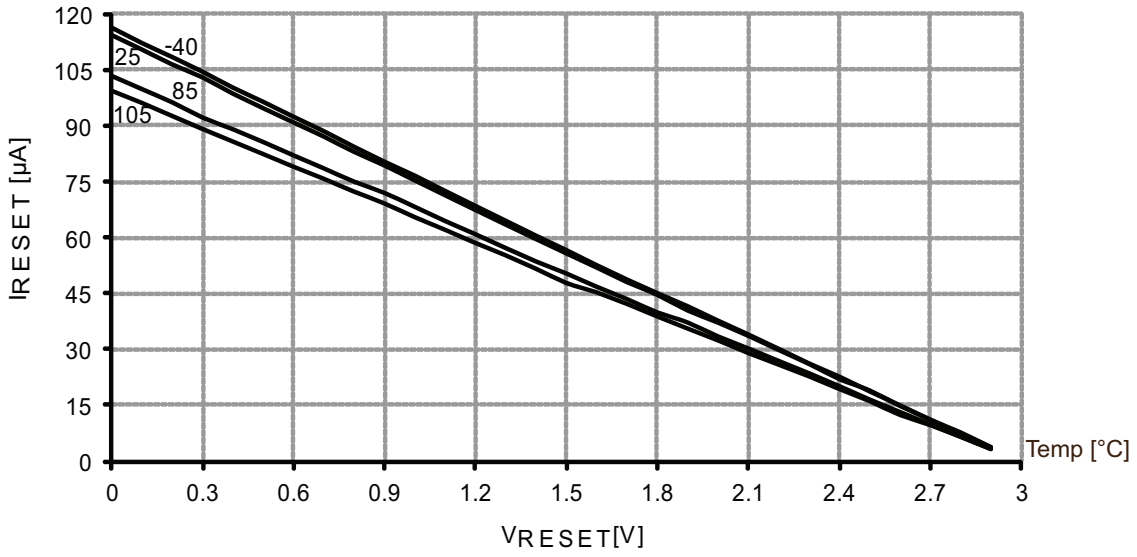
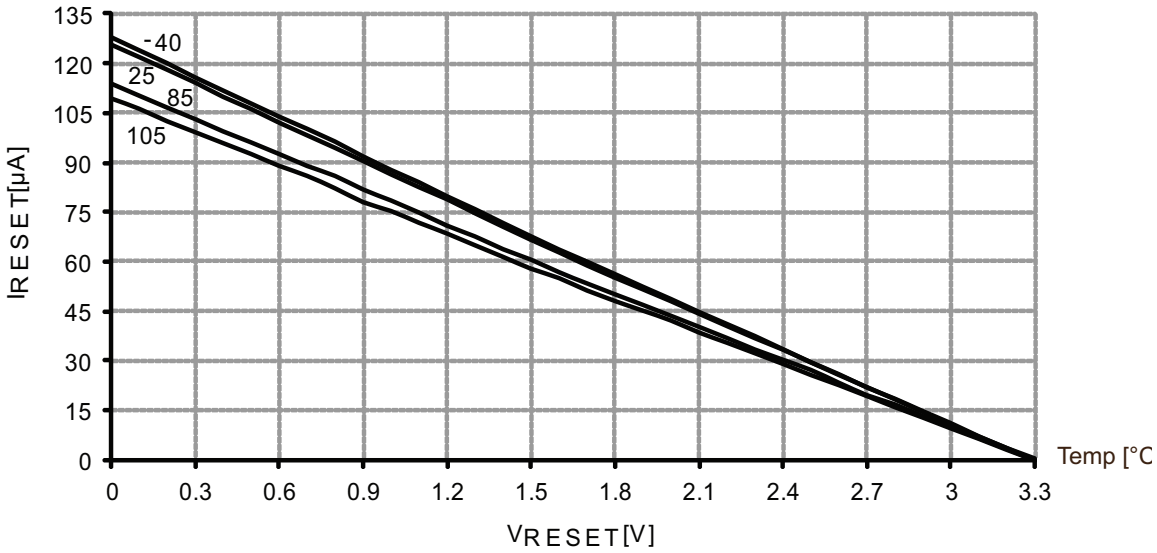


Figure 37-64. Reset pin pull-up resistor current vs. reset pin voltage.

V_{CC} = 3.3V.



37.1.10.5 32MHz internal oscillator calibrated to 48MHz

Figure 37-78. 48MHz internal oscillator frequency vs. temperature.

DFLL disabled.

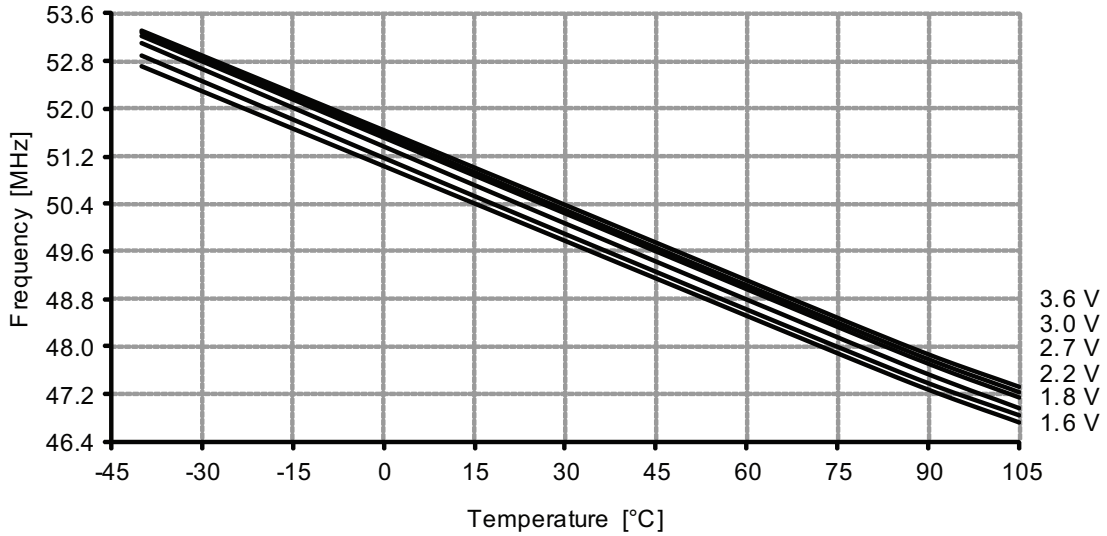


Figure 37-79. 48MHz internal oscillator frequency vs. temperature.

DFLL enabled, from the 32.768kHz internal oscillator.

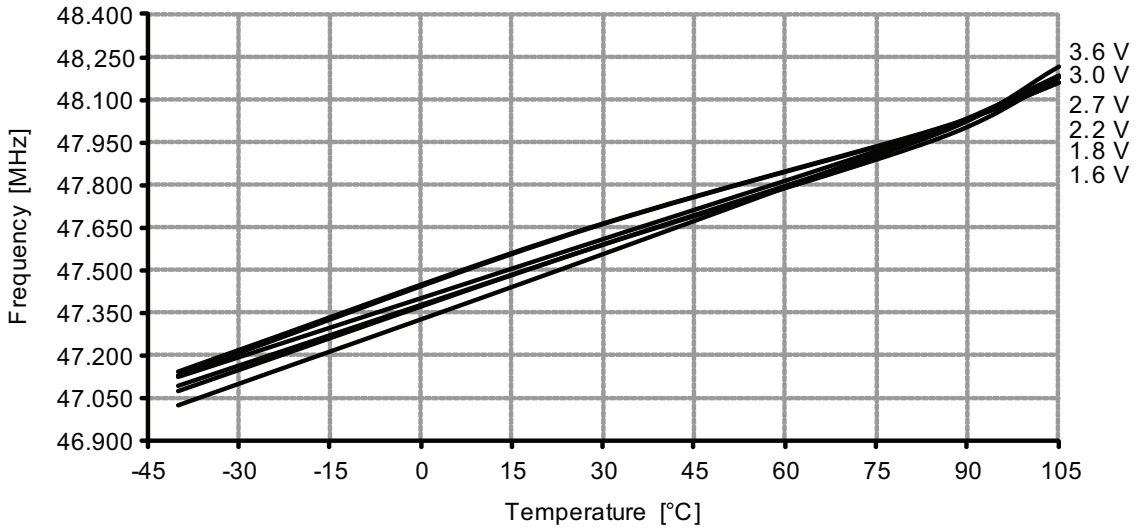


Figure 37-159. 32MHz internal oscillator CALA calibration step size.

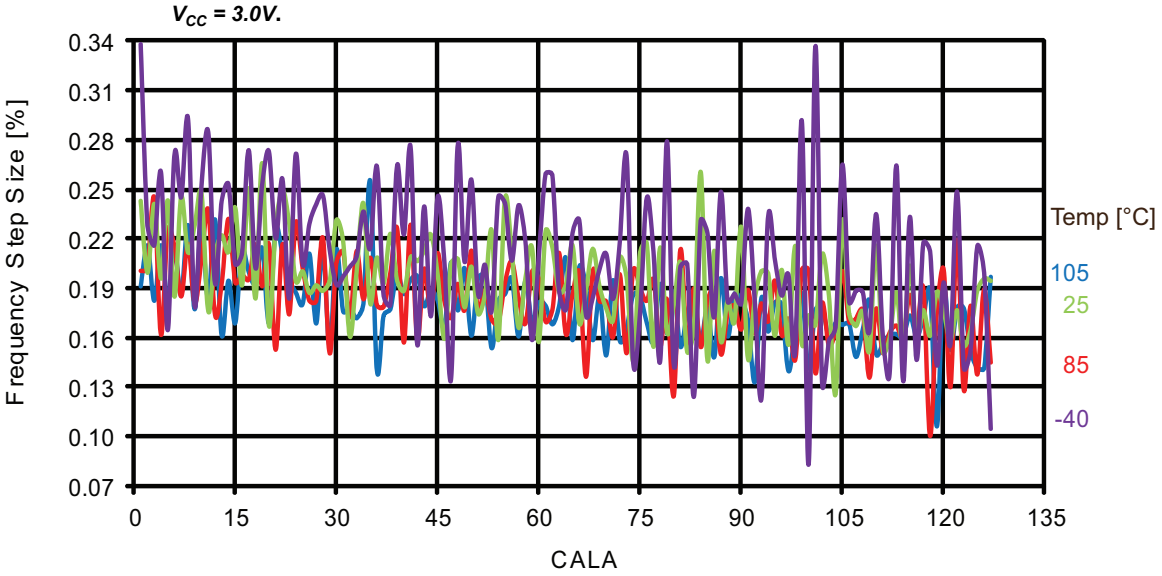
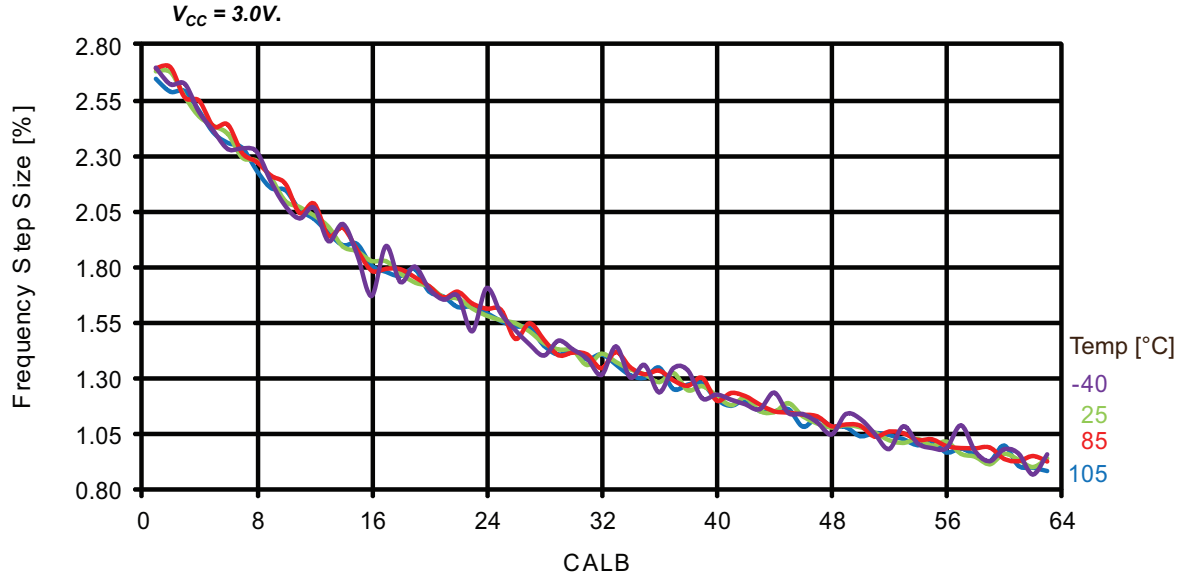


Figure 37-160. 32MHz internal oscillator frequency vs. CALB calibration value.



37.3 ATxmega192A3U

37.3.1 Current consumption

37.3.1.1 Active mode supply current

Figure 37-167. Active supply current vs. frequency.
f_{SYS} = 0 - 1MHz external clock, T = 25°C.

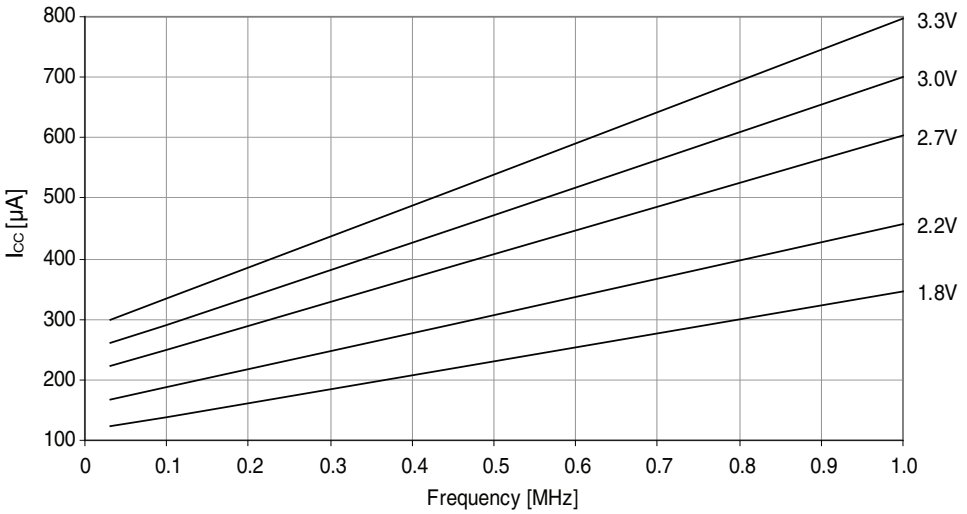


Figure 37-168. Active supply current vs. frequency.
f_{SYS} = 1 - 32MHz external clock, T = 25°C.

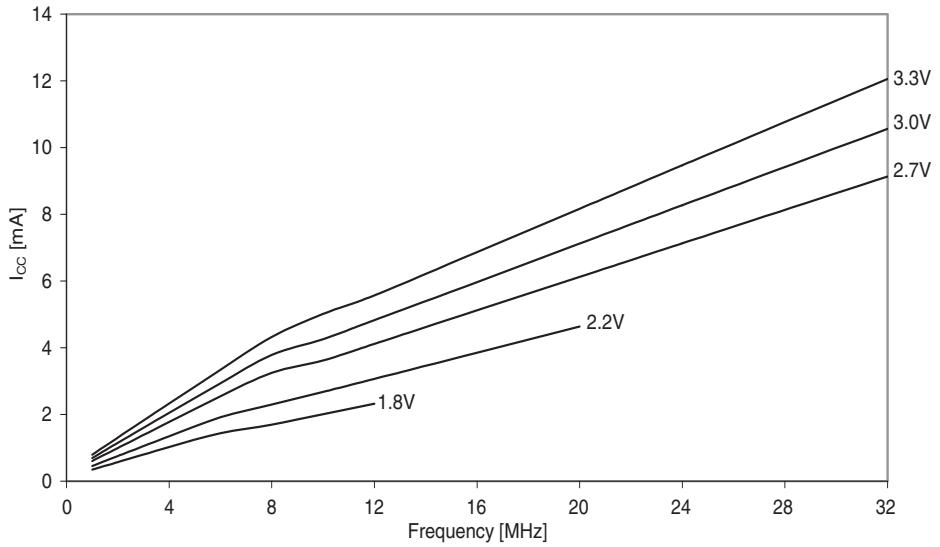


Figure 37-231. Reset pin input threshold voltage vs. V_{CC}

V_{IH} - Reset pin read as "1".

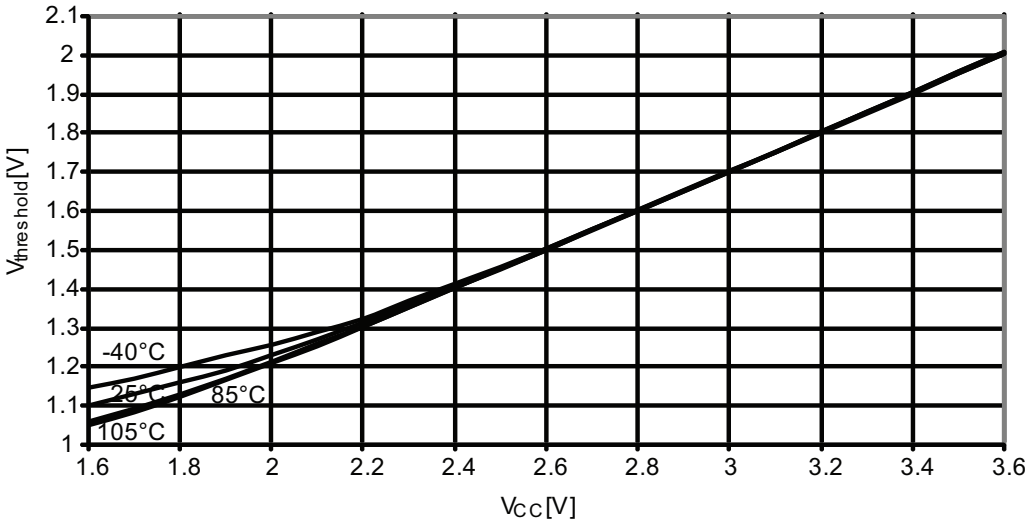
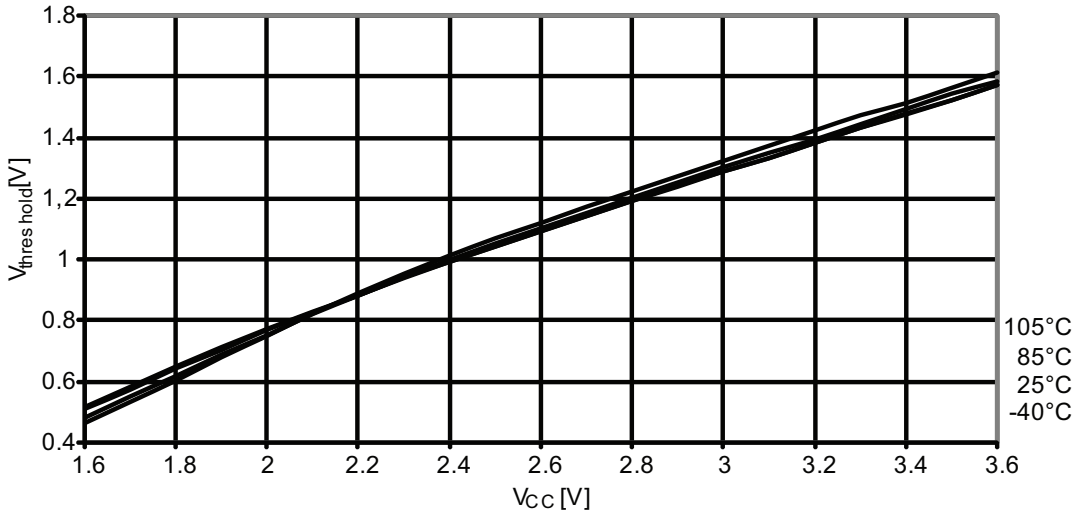


Figure 37-232. Reset pin input threshold voltage vs. V_{CC}.

V_{IL} - Reset pin read as "0".



37.3.10.5 32MHz internal oscillator calibrated to 48MHz

Figure 37-244. 48MHz internal oscillator frequency vs. temperature.
DFLL disabled.

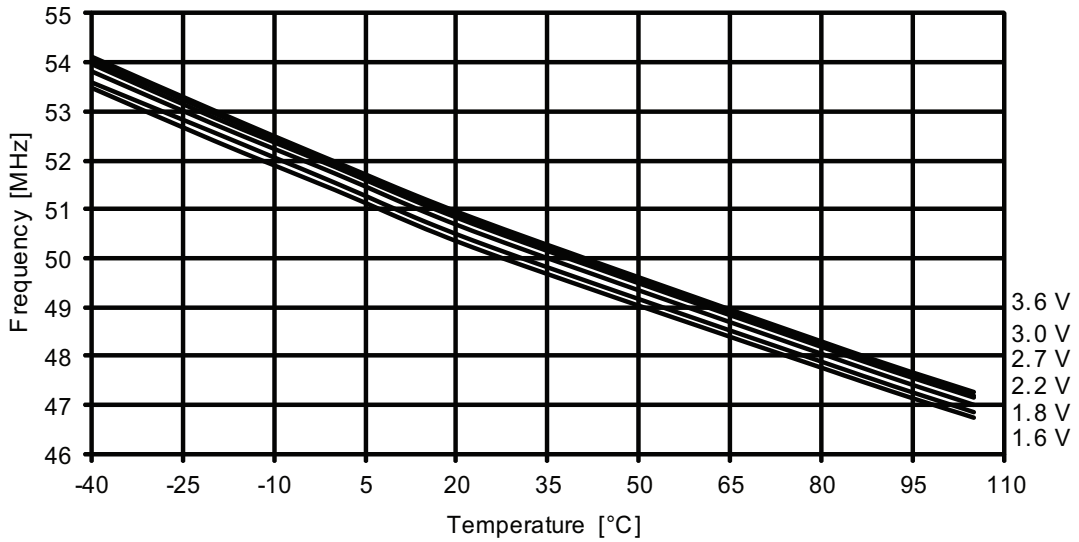


Figure 37-245. 48MHz internal oscillator frequency vs. temperature.
DFLL enabled, from the 32.768kHz internal oscillator.

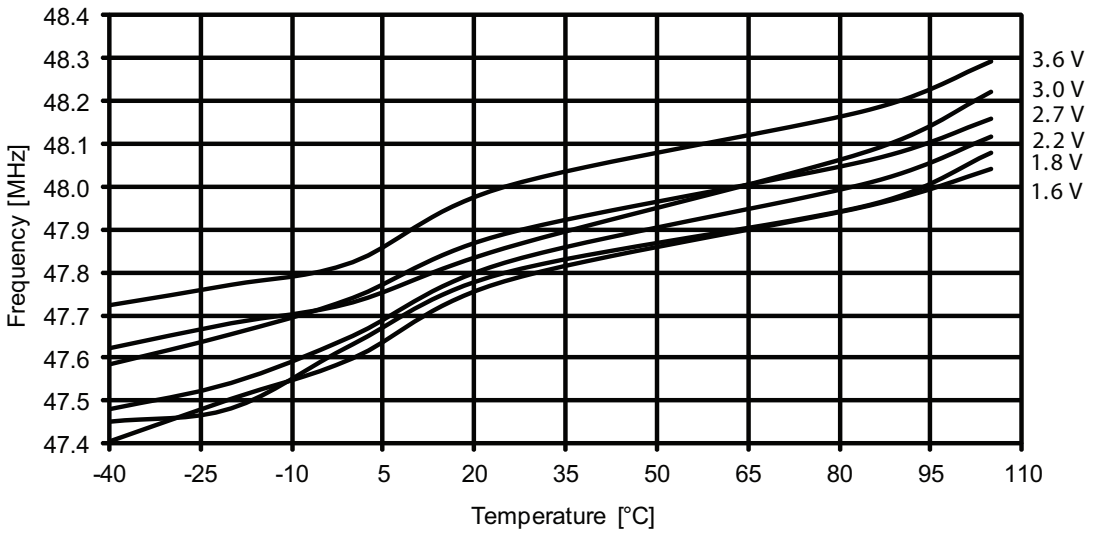


Figure 37-260. Idle mode supply current vs. V_{CC}.

f_{SYS} = 1MHz external clock.

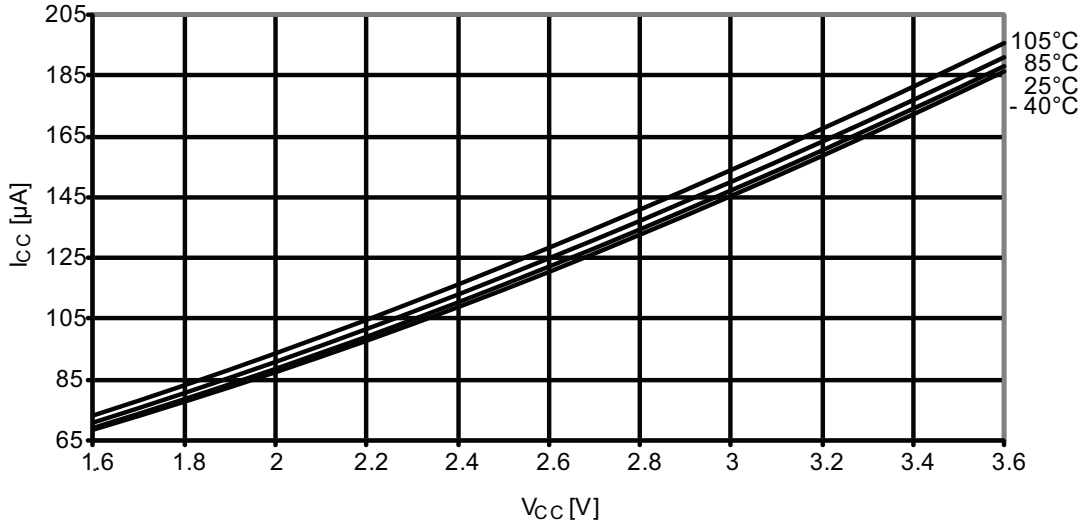


Figure 37-261. Idle mode supply current vs. V_{CC}.

f_{SYS} = 2MHz internal oscillator.

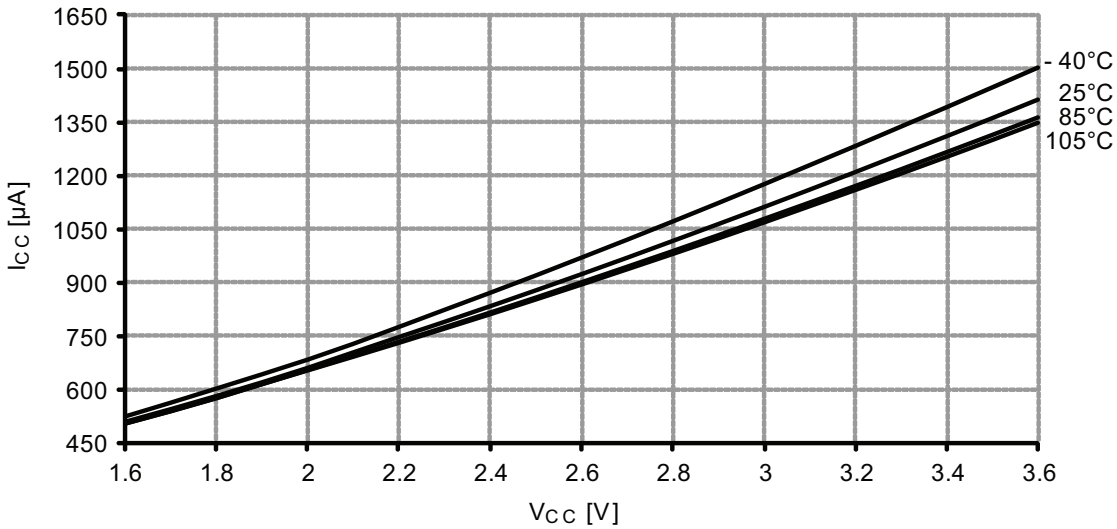


Figure 37-321. 2MHz internal oscillator frequency vs. temperature.

DFLL enabled, from the 32.768kHz internal oscillator.

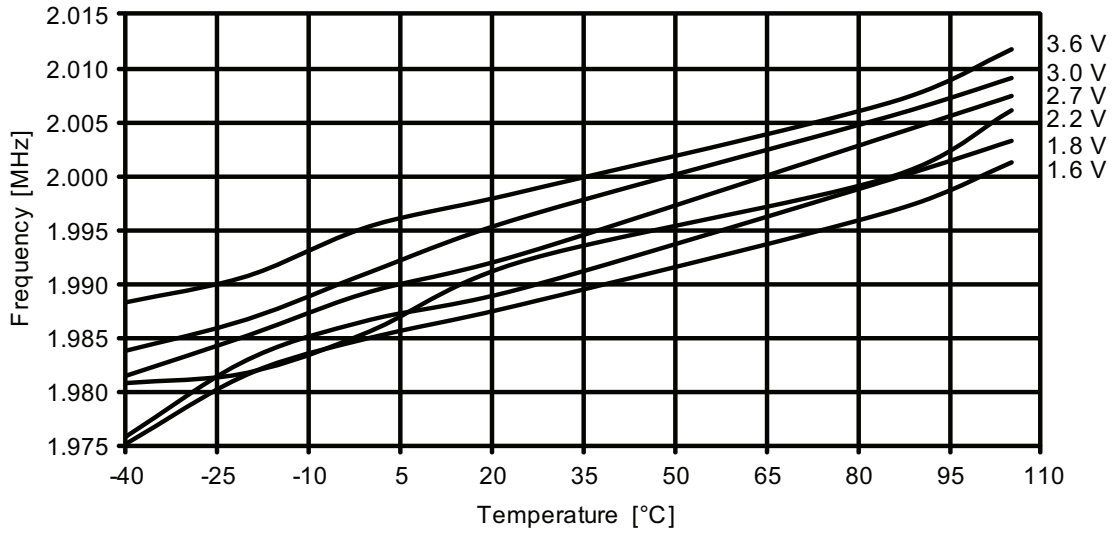


Figure 37-322. 2MHz internal oscillator CALA calibration step size.

V_{CC} = 3V.